

AMENDMENTS TO THE SPECIFICATION

Page 5, lines 6-23: please amend as follows:

Further, a method of manufacturing a CAM cell according to the present invention is characterized in that it comprises the steps of forming a device isolation film in a given region on a semiconductor substrate to define an active region and a device isolation region; defining the active region into a cell region and a peripheral circuit region by a given process; forming a tunnel oxide film and a first polysilicon film on the entire structure and then patterning the tunnel oxide film and the first polysilicon film so that the tunnel oxide film and the first polysilicon film can only remain in a given region of the cell region, thus defining a floating gate; forming an insulating film in which the oxide film and the nitride film are stacked on the entire structure to form a second polysilicon film; patterning the second polysilicon film and the insulating film so that they can remain only in a given region of the cell region and the (distinct) peripheral circuit region, thus forming a control gate in the cell region, a gate in the peripheral circuit region; and performing an impurity ion implantation process for a given region of the semiconductor substrate to form a source region and a drain region, so that a flash memory cell is formed in the cell region and a code address memory cell is formed in the peripheral circuit region.